## 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

### 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

## 3. Applications

- Class-D amplifiers
- DC-to-DC converters
- Motor control
- Server power supplies

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	74	W
Static charac	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$		-	2.43	3.5	mΩ
Dynamic cha	racteristics				·		·
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V;		-	5	-	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 14; Fig. 15		-	19	-	nC
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 100 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	54	mJ

[1] Continuous current is limited by package.



### N-channel 30 V 3.5 m $\Omega$ logic level MOSFET in LFPAK

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	<u> </u>	
3	S	source	a	G—(F)
4	G	gate	0.00	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PSMN3R5-30YL	'	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PSMN3R5-30YL	3R530

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C			30	V
$V_{DSM}$	peak drain-source voltage	$t_p \le 25 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 180 \text{ nJ};$ pulsed		-	35	V
$V_{DGR}$	drain-gate voltage	$25 ^{\circ}$ C ≤ T <sub>j</sub> ≤ 175 $^{\circ}$ C; R <sub>GS</sub> = 20 kΩ		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	74	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	86	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	447	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]		100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	447	Α
Avalanche r	uggedness					

#### N-channel 30 V 3.5 m $\Omega$ logic level MOSFET in LFPAK

Symbol	Parameter	Conditions	Min	Max	Unit
DO(AL)O		$I_D$ = 100 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	54	mJ

#### [1] Continuous current is limited by package.

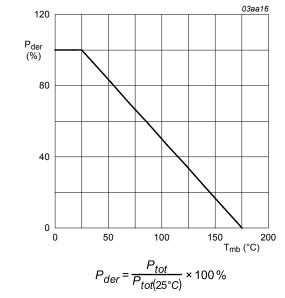
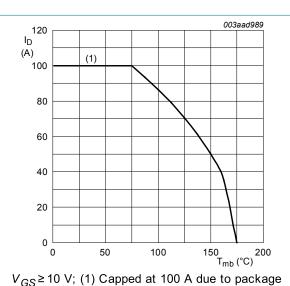
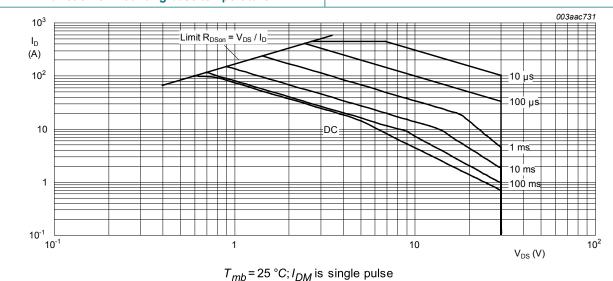


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



g. 2. Continuous drain current as a function of mounting base temperature



(1) Capped at 100 A due to package.

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.6	1.68	K/W

### N-channel 30 V 3.5 m $\Omega$ logic level MOSFET in LFPAK



## 10. Characteristics

**Table 7. Characteristics** 

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					<u> </u>
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 11; Fig. 12$	1.3	1.7	2.15	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C; Fig. 12	0.65	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 12$	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C	-	3.37	4.61	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 150 °C; Fig. 13	-	-	6	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C	-	2.43	3.5	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.53	1.5	Ω
Dynamic ch	naracteristics					'
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; Fig. 14; Fig. 15	-	19	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	37	-	nC
		I <sub>D</sub> = 10 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	41	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V;	-	6	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 14; Fig. 15	-	4	-	nC

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	2	-	nC
$Q_{GD}$	gate-drain charge		-	5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 12 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	2.4	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	2458	3441	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	532	718	pF
C <sub>rss</sub>	reverse transfer capacitance		-	252	353	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	33	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	50	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	45	-	ns
t <sub>f</sub>	fall time		-	18	-	ns
Source-dra	in diode			'		
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A/µs}$ ; $V_{GS} = 0 \text{ V}$ ;	-	37	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V	-	31	-	nC

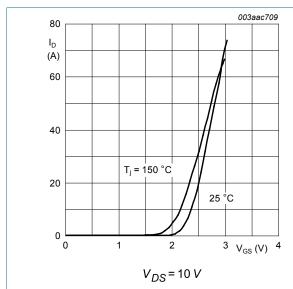


Fig. 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values

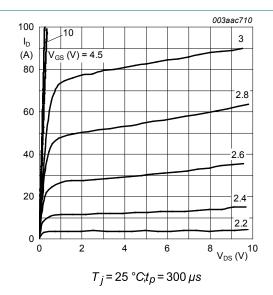


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

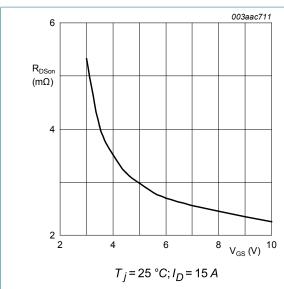


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

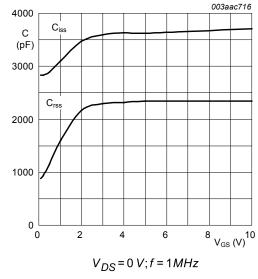


Fig. 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

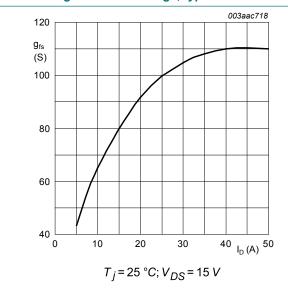


Fig. 9. Forward transconductance as a function of drain current; typical values

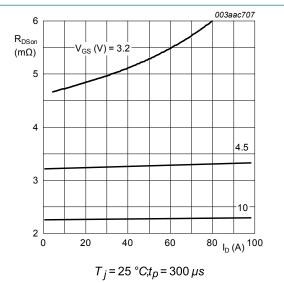


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

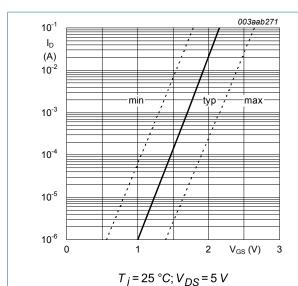


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

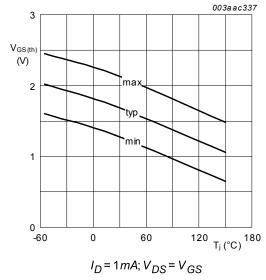


Fig. 12. Gate-source threshold voltage as a function of junction temperature

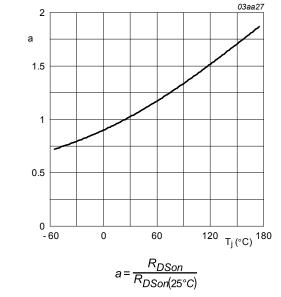


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

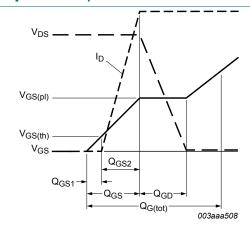


Fig. 14. Gate charge waveform definitions

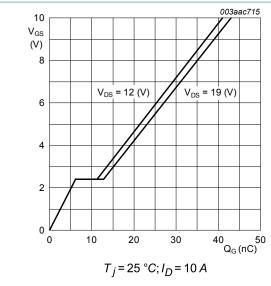


Fig. 15. Gate-source voltage as a function of gate charge; typical values

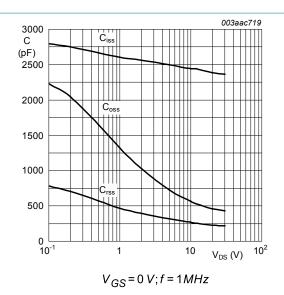


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

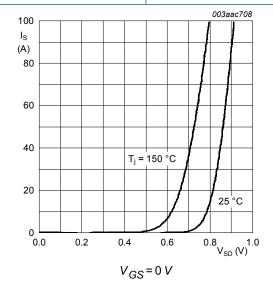
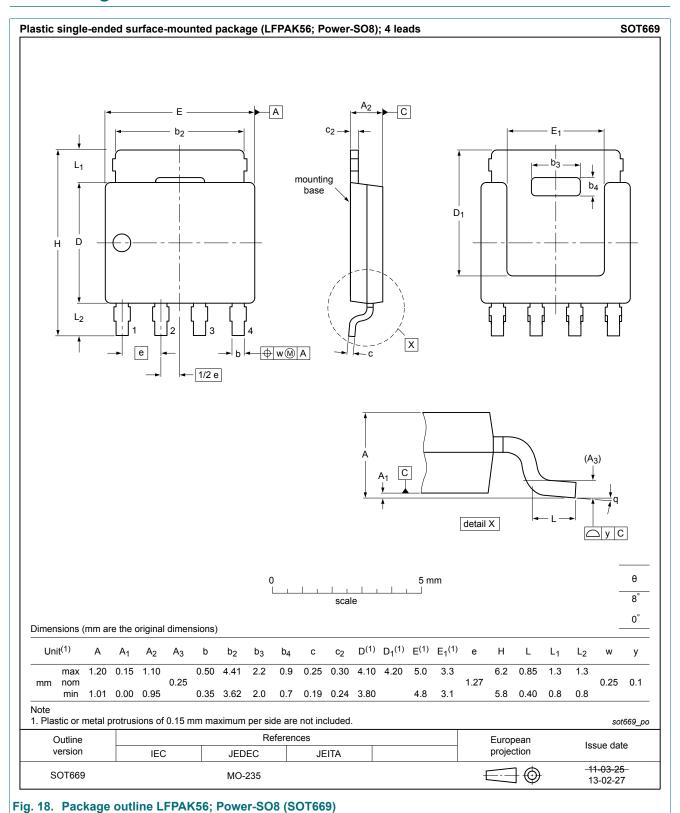


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

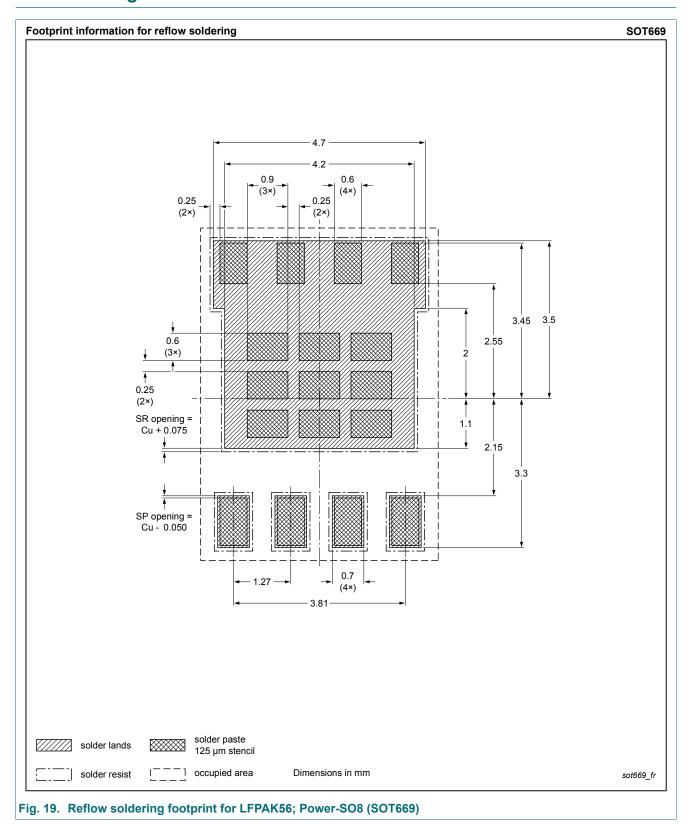
#### N-channel 30 V 3.5 m $\Omega$ logic level MOSFET in LFPAK

# 11. Package outline



### N-channel 30 V 3.5 m $\Omega$ logic level MOSFET in LFPAK

# 12. Soldering



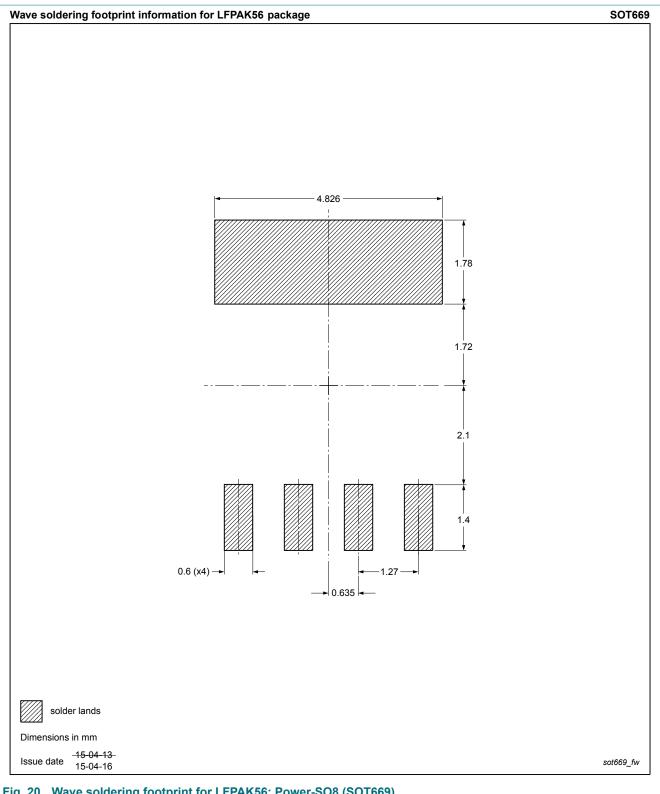


Fig. 20. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## N-channel 30 V 3.5 m $\Omega$ logic level MOSFET in LFPAK

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